

Amendments to the Claims:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

Listing of Claims:

1. (Currently Amended) ~~A~~The polishing medium for chemical-mechanical polishing according to claim 27, further comprising an oxidizing agent, a metal-oxide-dissolving agent, ~~a protective film-forming agent~~, ~~a water-soluble polymer~~, and water.

2. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim ~~4~~27, wherein said water-soluble polymer has a weight-average molecular weight of 500 or more.

3. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 2, wherein said water-soluble polymer comprises two or more polymers each having a weight-average molecular weight of 500 or more, wherein but a weight-average molecular weight of said polymers are different from each other.

4. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim ~~4~~27, which has a coefficient of kinetic friction of 0.25 or more.

5. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim 427, which has a Ubbelode's viscosity of 0.95 mPa's (0.95 cP) or more and 1.5 mPa's (1.5 cP) or less.

6. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim 427, which has a point-of-inflection pressure of 5 kPa (50 gf/cm²) or more.

7. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim 427, wherein said oxidizing agent is at least one of hydrogen peroxide, nitric acid, potassium periodate, hypochlorous acid and ozone water.

8. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 1, wherein said metal-oxide-dissolving agent is at least one of an organic acid, an organic-acid ester, an organic-acid ammonium salt and sulfuric acid.

9. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim 427, wherein said protective-film-forming agent is a nitrogen-containing compound.

10. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim 427, wherein said protective-film-forming agent is at

least one of a mercaptan, glucose and cellulose.

11. (Currently Amended) A polishing method comprising polishing a polishing object film of a metal or metal oxide with the polishing medium for chemical-mechanical polishing according to claim ~~4~~27.

12. (Previously Presented) The polishing method according to claim 11, wherein said polishing object film comprises at least one of copper, a copper alloy, a copper oxide and a copper alloy oxide.

13. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 2, which has a coefficient of kinetic friction of 0.25 or more.

14. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 13, which has a Ubbelode's viscosity of 0.95 mPa's (0.95 cP) or more and 1.5 mPa's (1.5 cP) or less.

15. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 14, which has a point-of-inflection pressure of 5 kPa (50 gf/cm²) or more.

16. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 2, which has a Ubbelode's viscosity of 0.95 mPa's (0.95

cP) or more and 1.5 mPa's (1.5 cP) or less.

17. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 2, which has a point-of-inflection pressure of 5 kPa (50 gf/cm²) or more.

18. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 9, wherein said water-soluble polymer is selected from the group consisting of polysaccharides, polycarboxylic acids and esters and salts thereof, and vinyl polymers.

19. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 10, wherein said water-soluble polymer is selected from the group consisting of pectic acid, agar, polymalic acid, polymethacrylic acid, polyacrylic acid, polyacrylamide, polyvinyl alcohol and polyvinyl pyrrolidone, and esters and ammonium salts thereof.

20. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim ~~4~~27, wherein said water-soluble polymer has a weight-average molecular weight of 1,500 or more.

21. (Currently Amended) The polishing medium for chemical-mechanical polishing according to claim ~~4~~27, wherein said water-soluble polymer has a weight-average molecular weight of 5,000 or more.

22. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 4, which has a coefficient of kinetic friction of 0.35 or more.

23. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 22, which has a coefficient of kinetic friction of 0.45 or more.

24. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 5, which has a Ubbelode's viscosity in the range of 0.96 to 1.3 mPa·s.

25. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 24, which has a Ubbelode's viscosity in the range of 0.97 to 1.0 mPa·s.

26. (Previously Presented) The polishing medium for chemical-mechanical polishing according to claim 6, which has a point-of-inflection pressure of 10 kPa (100 gf/cm²) or more.

27. (New) A polishing medium for chemical-mechanical polishing, comprising an oxidizing agent, a protective-film-forming agent, a water-soluble polymer, and water.

28. (New) The polishing medium for chemical-mechanical polishing according to claim 6, wherein said water-soluble polymer is selected from the group consisting of polysaccharides, polycarboxylic acids and esters and salts thereof, and vinyl polymers.

29. (New) The polishing medium for chemical-mechanical polishing according to claim 6, wherein said water-soluble polymer is selected from the group consisting of pectic acid, agar, polymalic acid, polymethacrylic acid, polyacrylic acid, polyacrylamide, polyvinyl alcohol and polyvinyl pyrrolidone, and esters and ammonium salts thereof.

30. (New) The polishing medium for chemical-mechanical polishing according to claim 9, wherein said nitrogen-containing compound is selected from the group consisting of ammonia, alkylamines, amino acids, imines, azoles, and salts thereof.

31. (New) The polishing medium for chemical-mechanical polishing according to claim 18, wherein said nitrogen-containing compound is selected from the group consisting of ammonia, alkylamines, amino acids, imines, azoles, and salts thereof.

32. (New) The polishing medium for chemical-mechanical polishing according to claim 1, wherein said protective-film-forming agent is at least one selected from the group consisting of chitosan, ethylenediaminetetraacetic acid, L-

tryptophane, cuperazone, triazinedithiol, benzotriazole, 4-hydroxybenzotriazole, 4-carboxyl-1H-benzotriazole butyl ester, tolyltriazole and naphthotriazole.